

# M/A-COM GaAs MMIC VSAT Power Amplifier 2.0W 14.0 - 14.5 GHz

## Features

- High Linear Gain: 22 dB Typ.
- High Saturated Output Power: +33 dBm Typ.
- High Power Added Efficiency: 22% Typ.
- High  $P_{1dB}$ : 32 dBm Typ.
- 50Ω Input/Output Broadband Matched
- Integrated Output Power Detector
- High Performance Ceramic Bolt Down Package

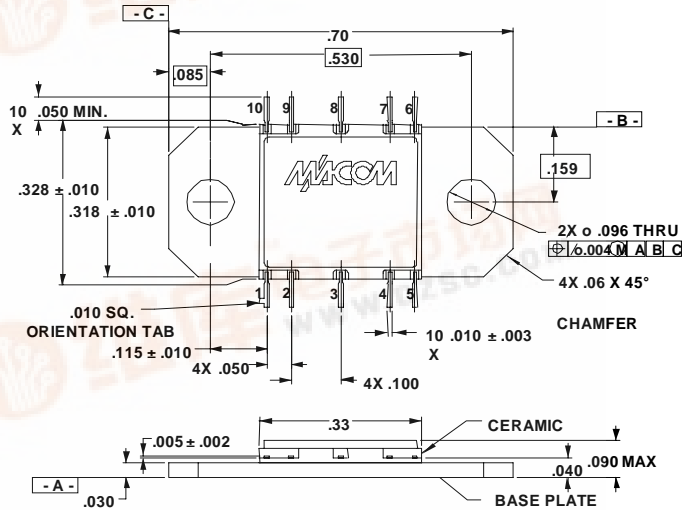
## Description

M/A-COM's AM42-0007 is a three-stage MMIC linear power amplifier in a ceramic bolt down style hermetic package. The AM42-0007 employs a fully matched chip with internally decoupled Gate and Drain bias networks and an output power detector. The AM42-0007 is designed to be operated from a constant voltage Drain supply.

The AM42-0007 is designed for use as an output stage or a driver, in applications for VSAT systems. This design is fully monolithic and requires a minimum of external components.

M/A-COM's AM42-0007 is fabricated using a mature 0.5 micron GaAs MESFET process. The process features full passivation for increased performance and reliability. This product is 100% RF tested to ensure compliance to performance specifications.

CR-15



- Notes: (unless otherwise specified)  
 1. Dimensions are in inches.  
 2. Tolerance: .XXX = ± 0.005  
 .XX = ± 0.010

## Ordering Information

Part Number	Package
AM42-0007	Ceramic Bolt Down Package

## Electrical Specifications: $T_C = +25^\circ\text{C}$ , $V_{DD} = +9\text{V}$ , $V_{GG} = -5.0\text{V}$ , $Z_0 = 50\Omega$ , Frequency = 14.0-14.5 GHz

Parameter	Abbv.	Test Conditions	Units	Min.	Typ.	Max.
Linear Gain	$G_L$	$P_{IN} \leq 0 \text{ dBm}$	dB	19	22	—
Input VSWR	$VSWR_{IN}$	$P_{IN} \leq 0 \text{ dBm}$	—	—	2.5:1	2.7:1
Output VSWR	$VSWR_{OU}$	$P_{IN} \leq 0 \text{ dBm}$	—	—	2.7:1	—
Saturated Output Power	$P_{SAT}$	$P_{IN} = +14 \text{ dBm}$	dBm	—	33	—
Output Power @	$P_{1dB}$	—	dBm	31	32	—
Output $IP_3$	$IP_3$	(Refer to Note 1)	dBm	—	41	—
Power Added Efficiency	PAE	$P_{IN} = +14 \text{ dBm}$	%	—	22	—
Bias Currents	$I_{GG}$	$P_{IN} = +14 \text{ dBm}$	mA	—	18	25
Thermal Resistance	$\theta_{JC}$	25°C Heat Sink	°C/W	—	9.5	—
Detector Output Voltage	$V_{det}$	$R_L = 10K\Omega$ , $P_{OUT} = +31 \text{ dBm}$	V	—	+3.5	—

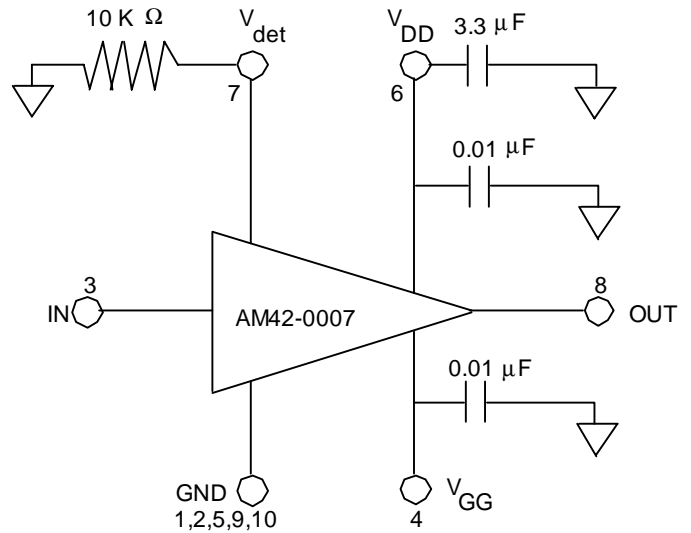
$IP_3$  is measured with two +24 dBm output tones @ 1 MHz spacing.



Absolute Maximum Ratings<sup>1,2,3,4</sup>

Parameter	Absolute Maximum
V <sub>DD</sub>	12 Volts
V <sub>GG</sub>	-10 Volts
Power Dissipation	13.2 W
RF Input Power	+23 dBm
Channel Temperature	150°C
Storage Temperature	-65°C to +150°C
I <sub>ds</sub>	2100 mA

1. Operation of this device outside any of these limits may cause permanent damage.
2. Case Temperature (T<sub>C</sub>) = +25°C.
3. Nominal bias is obtained by first connecting -5 volts to pin 4 (V<sub>GG</sub>), followed by connection +9 volts to pin 6 (V<sub>DD</sub>). Note sequence.
4. RF ground and thermal interface is the flange (case bottom). Adequate heat sinking is required.
5. No dc bias voltage appears at the RF ports.
6. The dc resistance at the input port is an open circuit and at the output port is a short circuit.
7. For optimum IP<sub>3</sub> performance, the V<sub>DD</sub> bypass capacitors should be placed within 0.5 inches of pin 6.

Typical Bias Configuration<sup>3,4,7</sup>

## Pin Configuration

Pin No.	Pin Name	Description
1	GND	DC and RF Ground
2	GND	DC and RF Ground
3	IN	RF Input
4	V <sub>GG</sub>	Gate Supply
5	GND	DC and RF Ground
6	V <sub>DD</sub>	Voltage Drain Supply
7	V <sub>det</sub>	Output Power Detector
8	OUT	RF Output
9	GND	DC and RF Ground
10	GND	DC and RF Ground

Typical Performance @ +25°C

Test Conditions are listed in the section “Electrical Specifications”.

